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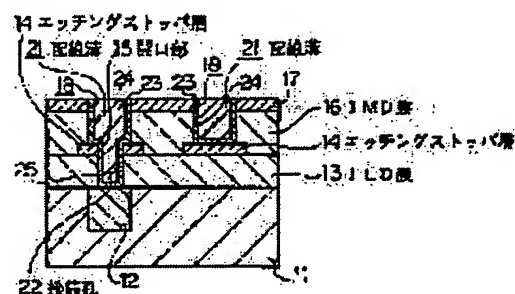
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(54) SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING IT

(57)Abstract:

PROBLEM TO BE SOLVED: To enable semiconductor device to be lessened in inter-wiring and inter-wiring layer effective dielectric constant and inter-wiring and inter-wiring layer capacitance.

SOLUTION: An insulating film (ILD film 13) which is interposed between wiring layers and provided with a connection hole, an insulating film (IMD film 16) which is interposed between wiring layers and provided with a wiring groove, and an etching stopper layer 14 interposed between the insulating films 13 and 16 are provided, where an opening 15 used for forming a connection hole 22 is provided in the etching stopper layer 14, and the etching stopper layer 14 is formed only under and around regions where wiring grooves 21 are each formed.



LEGAL STATUS

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